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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	3000
Number of Logic Elements/Cells	12000
Total RAM Bits	589824
Number of I/O	197
Number of Gates	-
Voltage - Supply	1.045V ~ 1.155V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	381-FBGA
Supplier Device Package	381-CABGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lfe5u-12f-6bg381c

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2. Architecture

2.1. Overview

Each ECP5/ECP5-5G device contains an array of logic blocks surrounded by Programmable I/O Cells (PIC). Interspersed between the rows of logic blocks are rows of sysMEM™ Embedded Block RAM (EBR) and rows of sysDSP™ Digital Signal Processing slices, as shown in [Figure 2.1](#) on page 13. The LFE5-85 devices have three rows of DSP slices, the LFE5-45 devices have two rows, and both LFE5-25 and LFE5-12 devices have one. In addition, the LFE5UM/LFE5UM5G devices contain SERDES Duals on the bottom of the device.

The Programmable Functional Unit (PFU) contains the building blocks for logic, arithmetic, RAM and ROM functions. The PFU block is optimized for flexibility, allowing complex designs to be implemented quickly and efficiently. Logic Blocks are arranged in a two-dimensional array.

The ECP5/ECP5-5G devices contain one or more rows of sysMEM EBR blocks. sysMEM EBRs are large, dedicated 18 Kb fast memory blocks. Each sysMEM block can be configured in a variety of depths and widths as RAM or ROM. In addition, ECP5/ECP5-5G devices contain up to three rows of DSP slices. Each DSP slice has multipliers and adder/accumulators, which are the building blocks for complex signal processing capabilities.

The ECP5 devices feature up to four embedded 3.2 Gb/s SERDES channels, and the ECP5-5G devices feature up to four embedded 5 Gb/s SERDES channels. Each SERDES channel contains independent 8b/10b encoding / decoding, polarity adjust and elastic buffer logic. Each group of two SERDES channels, along with its Physical Coding Sublayer (PCS) block, creates a dual DCU (Dual Channel Unit). The functionality of the SERDES/PCS duals can be controlled by SRAM cell settings during device configuration or by registers that are addressable during device operation. The registers in every dual can be programmed via the SERDES Client Interface (SCI). These DCUs (up to two) are located at the bottom of the devices.

Each PIC block encompasses two PIOs (PIO pairs) with their respective sysI/O buffers. The sysI/O buffers of the ECP5/ECP5-5G devices are arranged in seven banks (eight banks for LFE5-85 devices in caBGA756 and caBGA554 packages), allowing the implementation of a wide variety of I/O standards. One of these banks (Bank 8) is shared with the programming interfaces. Half of the PIO pairs on the left and right edges of the device can be configured as LVDS transmit pairs, and all pairs on left and right can be configured as LVDS receive pairs. The PIC logic in the left and right banks also includes pre-engineered support to aid in the implementation of high speed source synchronous standards such as XGMII, 7:1 LVDS, along with memory interfaces including DDR3 and LPDDR3.

The ECP5/ECP5-5G registers in PFU and sysI/O can be configured to be SET or RESET. After power up and the device is configured, it enters into user mode with these registers SET/RESET according to the configuration setting, allowing the device entering to a known state for predictable system function.

Other blocks provided include PLLs, DLLs and configuration functions. The ECP5/ECP5-5G architecture provides up to four Delay-Locked Loops (DLLs) and up to four Phase-Locked Loops (PLLs). The PLL and DLL blocks are located at the corners of each device.

The configuration block that supports features such as configuration bit-stream decryption, transparent updates and dual-boot support is located at the bottom of each device, to the left of the SERDES blocks. Every device in the ECP5/ECP5-5G family supports a sysCONFIG™ ports located in that same corner, powered by Vccio8, allowing for serial or parallel device configuration.

In addition, every device in the family has a JTAG port. This family also provides an on-chip oscillator and soft error detect capability. The ECP5 devices use 1.1 V and ECP5UM5G devices use 1.2 V as their core voltage.

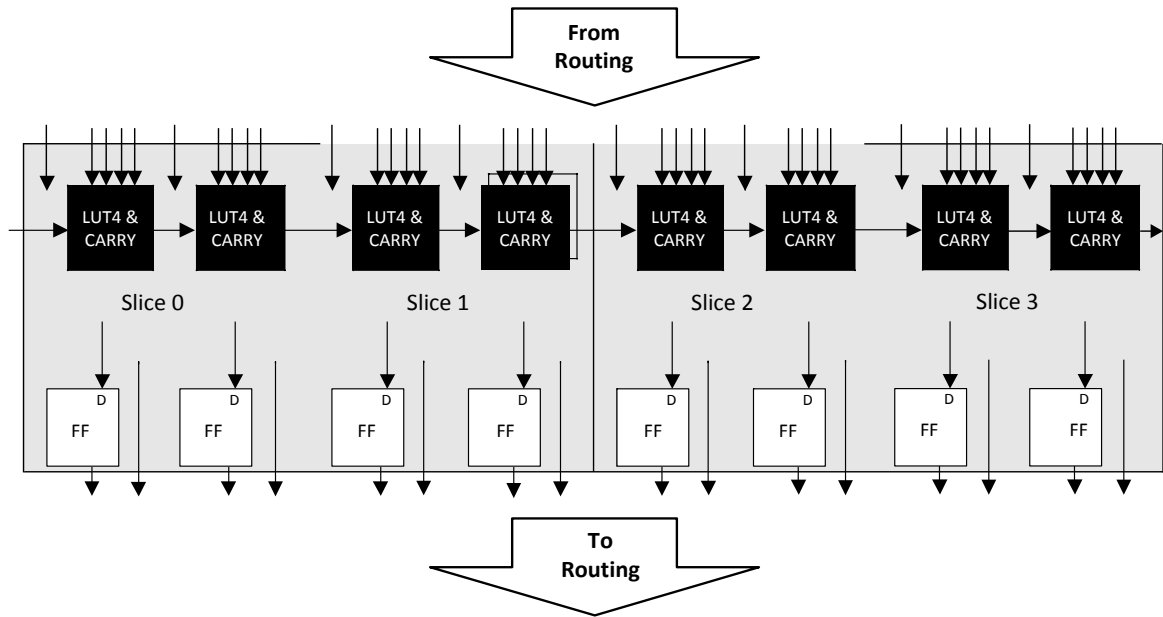


Figure 2.2. PFU Diagram

2.2.1. Slice

Each slice contains two LUT4s feeding two registers. In Distributed SRAM mode, Slice 0 through Slice 2 are configured as distributed memory, and Slice 3 is used as Logic or ROM. Table 2.1 shows the capability of the slices along with the operation modes they enable. In addition, each PFU contains logic that allows the LUTs to be combined to perform functions such as LUT5, LUT6, LUT7 and LUT8. There is control logic to perform set/reset functions (programmable as synchronous/ asynchronous), clock select, chip-select and wider RAM/ROM functions.

Table 2.1. Resources and Modes Available per Slice

Slice	PFU (Used in Distributed SRAM)		PFU (Not used as Distributed SRAM)	
	Resources	Modes	Resources	Modes
Slice 0	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 1	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 2	2 LUT4s and 2 Registers	RAM	2 LUT4s and 2 Registers	Logic, Ripple, ROM
Slice 3	2 LUT4s and 2 Registers	Logic, Ripple, ROM	2 LUT4s and 2 Registers	Logic, Ripple, ROM

Figure 2.3 shows an overview of the internal logic of the slice. The registers in the slice can be configured for positive/negative and edge triggered or level sensitive clocks. Each slice has 14 input signals, 13 signals from routing and one from the carry-chain (from the adjacent slice or PFU). There are five outputs, four to routing and one to carry-chain (to the adjacent PFU). There are two inter slice/ PFU output signals that are used to support wider LUT functions, such as LUT6, LUT7 and LUT8. Table 2.2 and Figure 2.3 list the signals associated with all the slices. Figure 2.4 on page 16 shows the connectivity of the inter-slice/PFU signals that support LUT5, LUT6, LUT7 and LUT8.

2.7. DDRDLL

Every DDRDLL (master DLL block) can generate phase shift code representing the amount of delay in a delay block that corresponding to 90° phase of the reference clock input. The reference clock can be either from PLL, or input pin. This code is used in the DQSBUF block that controls a set of DQS pin groups to interface with DDR memory (slave DLL). There are two DDRDLLs that supply two sets of codes (for two different reference clock frequencies) to each side of the I/Os (at each of the corners). The DQSBUF uses this code to controls the DQS input of the DDR memory to 90° shift to clock DQs at the center of the data eye for DDR memory interface.

The code is also sent to another slave DLL, DLLDEL, that takes a clock input and generates a 90° shift clock output to drive the clocking structure. This is useful to interface edge-aligned Generic DDR, where 90° clocking needs to be created. Figure 2.10 shows DDRDLL functional diagram.

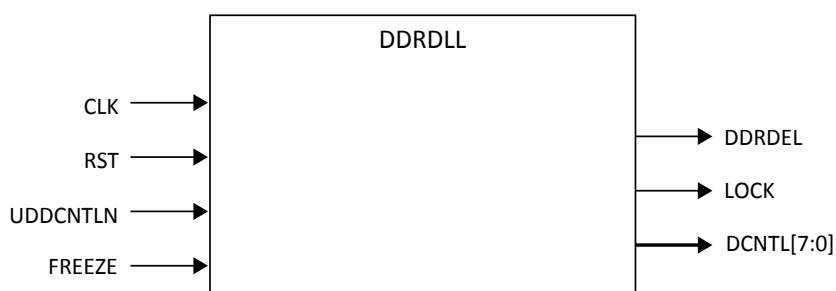


Figure 2.10. DDRDLL Functional Diagram

Table 2.5. DDRDLL Ports List

Port Name	Type	Description
CLK	Input	Reference clock input to the DDRDLL. Should run at the same frequency as the clock to the delay code.
RST	Input	Reset Input to the DDRDLL.
UDDCNTLN	Input	Update Control to update the delay code. The code is the DCNTL[7:0] outputs. These outputs are updated when the UDDCNTLN signal is LOW.
FREEZE	Input	FREEZE goes high and, without a glitch, turns off the DLL internal clock and the ring oscillator output clock. When FREEZE goes low, it turns them back on.
DDRDEL	Output	The delay codes from the DDRDLL to be used in DQSBUF or DLLDEL.
LOCK	Output	Lock output to indicate the DDRDLL has valid delay output.
DCNTL [7:0]	Output	The delay codes from the DDRDLL available for the user IP.

There are four identical DDRDLLs, one in each of the four corners in LFE5-85 and LFE5-45 devices, and two DDRDLLs in both LFE5-25 & LFE5-12 devices in the upper two corners. Each DDRDLL can generate delay code based on the reference frequency. The slave DLL (DQSBUF and DLLDEL) use the code to delay the signal, to create the phase shifted signal used for either DDR memory, to create 90° shift clock. Figure 2.11 shows the DDRDLL and the slave DLLs on the top level view.



ECP5/ECP5-5G devices contain a number of sysMEM Embedded Block RAM (EBR). The EBR consists of an 18 Kb RAM with memory core, dedicated input registers and output registers with separate clock and clock enable. Each EBR includes functionality to support true dual-port, pseudo dual-port, single-port RAM, ROM and FIFO buffers (via external PFUs).

The sysMEM block can implement single port, dual port or pseudo dual port memories. Each block can be used in a variety of depths and widths as listed in [Table 2.6](#) on page 25. FIFOs can be implemented in sysMEM EBR blocks by implementing support logic with PFUs. The EBR block facilitates parity checking by supporting an optional parity bit for each data byte. EBR blocks provide byte-enable support for configurations with 18-bit and 36-bit data widths. For more information, refer to [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#).

2.11.1.1. Input FIFO

The ECP5/ECP5-5G PIO has dedicated input FIFO per single-ended pin for input data register for DDR Memory interfaces. The FIFO resides before the gearing logic. It transfers data from DQS domain to continuous ECLK domain. On the Write side of the FIFO, it is clocked by DQS clock which is the delayed version of the DQS Strobe signal from DDR memory. On the Read side of FIFO, it is clocked by ECLK. ECLK may be any high speed clock with identical frequency as DQS (the frequency of the memory chip). Each DQS group has one FIFO control block. It distributes FIFO read/write pointer to every PIC in same DQS group. DQS Grouping and DQS Control Block is described in [DDR Memory Support](#) section on page 35.

Table 2.8. Input Block Port Description

Name	Type	Description
D	Input	High Speed Data Input
Q[1:0]/Q[3:0]/Q[6:0]	Output	Low Speed Data to the device core
RST	Input	Reset to the Output Block
SCLK	Input	Slow Speed System Clock
ECLK	Input	High Speed Edge Clock
DQS	Input	Clock from DQS control Block used to clock DDR memory data
ALIGNWD	Input	Data Alignment signal from device core.

2.11.2. Output Register Block

The output register block registers signal from the core of the device before they are passed to the sysIO buffers. ECP5/ECP5-5G output data path has output programmable flip flops and output gearing logic. On the left and right sides, the output register block can support 1x, 2x and 7:1 gearing enabling high speed DDR interfaces and DDR memory interfaces. On the top side, the banks support 1x gearing. ECP5/ECP5-5G output data path diagram is shown in [Figure 2.19](#). The programmable delay cells are also available in the output data path.

For detailed description of the output register block modes and usage, refer to [ECP5 and ECP5-5G High-Speed I/O Interface \(TN1265\)](#).

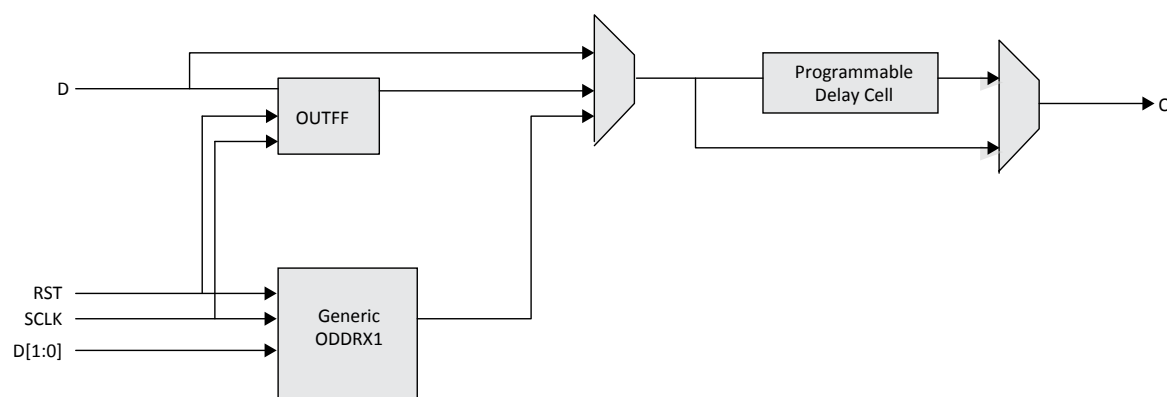


Figure 2.19. Output Register Block on Top Side

2.14. sysI/O Buffer

Each I/O is associated with a flexible buffer referred to as a sysI/O buffer. These buffers are arranged around the periphery of the device in groups referred to as banks. The sysI/O buffers allow users to implement the wide variety of standards that are found in today's systems including LVDS, HSUL, BLVDS, SSTL Class I and II, LVCMOS, LVTTTL, LVPECL, and MIPI.

2.14.1. sysI/O Buffer Banks

ECP5/ECP5-5G devices have seven sysI/O buffer banks, two banks per side at Top, Left and Right, plus one at the bottom left side. The bottom left side bank (Bank 8) is a shared I/O bank. The I/Os in that bank contains both dedicated and shared I/O for sysConfig function. When a shared pin is not used for configuration, it is available as a user I/O. For LFE5-85 devices, there is an additional I/O bank (Bank 4) that is not available in other device in the family.

In ECP5/ECP5-5G devices, the Left and Right sides are tailored to support high performance interfaces, such as DDR2, DDR3, LPDDR2, LPDDR3 and other high speed source synchronous standards. The banks on the Left and Right sides of the devices feature LVDS input and output buffers, data-width gearing, and DQSBUF block to support DDR2/3 and LPDDR2/3 interfaces. The I/Os on the top and bottom banks do not have LVDS input and output buffer, and gearing logic, but can use LVCMOS to emulate most of differential output signaling.

Each sysIO bank has its own I/O supply voltage (V_{CCIO}). In addition, the banks on the Left and Right sides of the device, have voltage reference input (shared I/O pin), V_{REF1} per bank, which allow it to be completely independent of each other. The V_{REF} voltage is used to set the threshold for the referenced input buffers, such as SSTL. Figure 2.25 shows the seven banks and their associated supplies.

In ECP5/ECP5-5G devices, single-ended output buffers and ratioed input buffers (LVTTTL, and LVCMOS) are powered using V_{CCIO} . LVTTTL, LVCMOS33, LVCMOS25 and LVCMOS12 can also be set as fixed threshold inputs independent of V_{CCIO} .

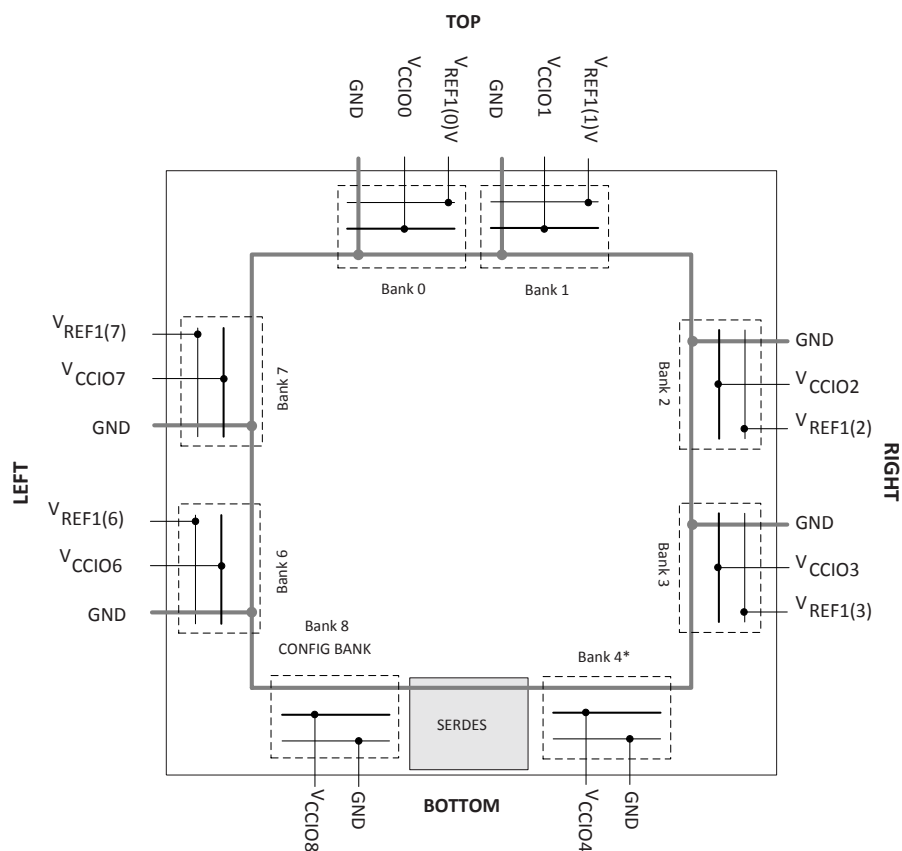


Figure 2.25. ECP5/ECP5-5G Device Family Banks

3.3. Power Supply Ramp Rates

Table 3.3. Power Supply Ramp Rates

Symbol	Parameter	Min	Typ	Max	Unit
t_{RAMP}	Power Supply ramp rates for all supplies	0.01	—	10	V/ms

Note: Assumes monotonic ramp rates.

3.4. Power-On-Reset Voltage Levels

Table 3.4. Power-On-Reset Voltage Levels

Symbol	Parameter			Min	Typ	Max	Unit
V_{PORUP}	All Devices	Power-On-Reset ramp-up trip point (Monitoring V_{CC} , V_{CCAUX} , and V_{CCIO8})	V_{CC}	0.90	—	1.00	V
			V_{CCAUX}	2.00	—	2.20	V
			V_{CCIO8}	0.95	—	1.06	V
V_{PORDN}	All Devices	Power-On-Reset ramp-down trip point (Monitoring V_{CC} , and V_{CCAUX})	V_{CC}	0.77	—	0.87	V
			V_{CCAUX}	1.80	—	2.00	V

Notes:

- These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
- Only V_{CCIO8} has a Power-On-Reset ramp up trip point. All other V_{CCIOs} do not have Power-On-Reset ramp up detection.
- V_{CCIO8} does not have a Power-On-Reset ramp down detection. V_{CCIO8} must remain within the Recommended Operating Conditions to ensure proper operation.

3.5. Power up Sequence

Power-On-Reset (POR) puts the ECP5/ECP5-5G device in a reset state. POR is released when V_{CC} , V_{CCAUX} , and V_{CCIO8} are ramped above the V_{PORUP} voltage, as specified above.

V_{CCIO8} controls the voltage on the configuration I/O pins. If the ECP5/ECP5-5G device is using Master SPI mode to download configuration data from external SPI Flash, it is required to ramp V_{CCIO8} above V_{IH} of the external SPI Flash, before at least one of the other two supplies (V_{CC} and/or V_{CCAUX}) is ramped to V_{PORUP} voltage level. If the system cannot meet this power up sequence requirement, and requires the V_{CCIO8} to be ramped last, then the system must keep either PROGRAMN or INITN pin LOW during power up, until V_{CCIO8} reaches V_{IH} of the external SPI Flash. This ensures the signals driven out on the configuration pins to the external SPI Flash meet the V_{IH} voltage requirement of the SPI Flash. For LFE5UM/LFE5UM5G devices, it is required to power up V_{CCA} , before V_{CCAUXA} is powered up.

3.6. Hot Socketing Specifications

Table 3.5. Hot Socketing Specifications

Symbol	Parameter	Condition	Min	Typ	Max	Unit
IDK_HS	Input or I/O Leakage Current for Top and Bottom Banks Only	$0 \leq V_{IN} \leq V_{IH} \text{ (Max)}$	—	—	± 1	mA
IDK	Input or I/O Leakage Current for Left and Right Banks Only	$0 \leq V_{IN} < V_{CCIO}$	—	—	± 1	mA
		$V_{CCIO} \leq V_{IN} \leq V_{CCIO} + 0.5 \text{ V}$	—	18	—	mA

Notes:

- V_{CC} , V_{CCAUX} and V_{CCIO} should rise/fall monotonically.
- I_{DK} is additive to I_{PU} , I_{PW} or I_{BH} .
- LVC MOS and LV TTL only.
- Hot socket specification defines when the hot socketed device's junction temperature is at 85 °C or below. When the hot socketed device's junction temperature is above 85 °C, the I_{DK} current can exceed ± 1 mA.

3.10. Supply Current (Standby)

Over recommended operating conditions.

Table 3.8. ECP5/ECP5-5G Supply Current (Standby)

Symbol	Parameter	Device	Typical	Unit
I _{CC}	Core Power Supply Current	LFE5U-12F/ LFE5U-25F/ LFE5UM-25F	77	mA
		LFE5UM5G-25F	77	mA
		LFE5U-45F/ LFE5UM-45F	116	mA
		LFE5UM5G-45F	116	mA
		LFE5U-85F/ LFE5UM-85F	212	mA
		LFE5UM5G-85F	212	mA
I _{CCAUX}	Auxiliary Power Supply Current	LFE5U-12F/ LFE5U-25F/ LFE5UM-25F/ LFE5UM5G-25F	16	mA
		LFE5U-45F/ LFE5UM-45F/ LFE5UM5G-45F	17	mA
		LFE5U-85F/ LFE5UM-85F/ LFE5UM5G-85F	26	mA
I _{CCIO}	Bank Power Supply Current (Per Bank)	LFE5U-12F/ LFE5U-25F/ LFE5UM-25F/ LFE5UM5G-25F	0.5	mA
		LFE5U-45F/ LFE5UM-45F/ LFE5UM5G-45F	0.5	mA
		LFE5U-85F/ LFE5UM-85F/ LFE5UM5G-85F	0.5	mA
I _{CCA}	SERDES Power Supply Current (Per Dual)	LFE5UM-25F	11	mA
		LFE5UM5G-25F	12	mA
		LFE5UM-45F	9.5	mA
		LFE5UM5G-45F	11	mA
		LFE5UM-85F	9.5	mA
		LFE5UM5G-85F	11	mA

Notes:

- For further information on supply current, see the list of technical documentation in [Supplemental Information](#) section on page 102.
- Assumes all outputs are tristated, all inputs are configured as LVCMOS and held at the V_{CCIO} or GND.
- Frequency 0 Hz.
- Pattern represents a “blank” configuration data file.
- T_J = 85 °C, power supplies at nominal voltage.
- To determine the ECP5/ECP5-5G peak start-up current, use the Power Calculator tool in the Lattice Diamond Design Software.

Table 3.20. Register-to-Register Performance

Function	–8 Timing	Unit
Basic Functions		
16-Bit Decoder	441	MHz
32-Bit Decoder	441	MHz
64-Bit Decoder	332	MHz
4:1 Mux	441	MHz
8:1 Mux	441	MHz
16:1 Mux	441	MHz
32:1 Mux	441	MHz
8-Bit Adder	441	MHz
16-Bit Adder	441	MHz
64-Bit Adder	441	MHz
16-Bit Counter	384	MHz
32-Bit Counter	317	MHz
64-Bit Counter	263	MHz
64-Bit Accumulator	288	MHz
Embedded Memory Functions		
1024x18 True-Dual Port RAM (Write Through or Normal), with EBR Output Registers	272	MHz
1024x18 True-Dual Port RAM (Read-Before-Write), with EBR Output Registers	214	MHz
Distributed Memory Functions		
16 x 2 Pseudo-Dual Port or 16 x 4 Single Port RAM (One PFU)	441	MHz
16 x 4 Pseudo-Dual Port (Two PFUs)	441	MHz
DSP Functions		
9 x 9 Multiplier (All Registers)	225	MHz
18 x 18 Multiplier (All Registers)	225	MHz
36 x 36 Multiplier (All Registers)	225	MHz
18 x 18 Multiply-Add/Sub (All Registers)	225	MHz
18 x 18 Multiply/Accumulate (Input and Output Registers)	225	MHz

Notes:

1. These functions were generated using Lattice Diamond design software tool. Exact performance may vary with the device and the design software tool version. The design software tool uses internal parameters that have been characterized but are not tested on every device.
2. Commercial timing numbers are shown. Industrial numbers are typically slower and can be extracted from Lattice Diamond design software tool.

3.16. Derating Timing Tables

Logic timing provided in the following sections of this data sheet and the Diamond design tools are worst case numbers in the operating range. Actual delays at nominal temperature and voltage for best case process, can be much better than the values given in the tables. The Diamond design tool can provide logic timing numbers at a particular temperature and voltage.

Table 3.22. ECP5/ECP5-5G External Switching Characteristics (Continued)

Parameter	Description	Device	-8		-7		-6		Unit
			Min	Max	Min	Max	Min	Max	
t_{H_DELPLL}	Clock to Data Hold - PIO Input Register with Data Input Delay	All Devices	0	—	0	—	0	—	ns
Generic DDR Input									
Generic DDRX1 Inputs With Clock and Data Centered at Pin (GDDR1_RX.SCLK.Centered) Using PCLK Clock Input - Figure 3.6									
$t_{SU_GDDR1_centered}$	Data Setup Before CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$t_{HD_GDDR1_centered}$	Data Hold After CLK Input	All Devices	0.52	—	0.52	—	0.52	—	ns
$f_{DATA_GDDR1_centered}$	GDDR1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX_GDDR1_centered}$	GDDR1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX1 Inputs With Clock and Data Aligned at Pin (GDDR1_RX.SCLK.Aligned) Using PCLK Clock Input - Figure 3.7									
$t_{SU_GDDR1_aligned}$	Data Setup from CLK Input	All Devices	—	-0.55	—	-0.55	—	-0.55	ns + 1/2 UI
$t_{HD_GDDR1_aligned}$	Data Hold from CLK Input	All Devices	0.55	—	0.55	—	0.55	—	ns + 1/2 UI
$f_{DATA_GDDR1_aligned}$	GDDR1 Data Rate	All Devices	—	500	—	500	—	500	Mb/s
$f_{MAX_GDDR1_aligned}$	GDDR1 CLK Frequency (SCLK)	All Devices	—	250	—	250	—	250	MHz
Generic DDRX2 Inputs With Clock and Data Centered at Pin (GDDR2_RX.ECLK.Centered) Using PCLK Clock Input, Left and Right sides Only - Figure 3.6									
$t_{SU_GDDR2_centered}$	Data Setup before CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$t_{HD_GDDR2_centered}$	Data Hold after CLK Input	All Devices	0.321	—	0.403	—	0.471	—	ns
$f_{DATA_GDDR2_centered}$	GDDR2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX_GDDR2_centered}$	GDDR2 CLK Frequency (ECLK)	All Devices	—	400	—	350	—	312	MHz
Generic DDRX2 Inputs With Clock and Data Aligned at Pin (GDDR2_RX.ECLK.Aligned) Using PCLK Clock Input, Left and Right sides Only - Figure 3.7									
$t_{SU_GDDR2_aligned}$	Data Setup from CLK Input	All Devices	—	-0.344	—	-0.42	—	-0.495	ns + 1/2 UI
$t_{HD_GDDR2_aligned}$	Data Hold from CLK Input	All Devices	0.344	—	0.42	—	0.495	—	ns + 1/2 UI
$f_{DATA_GDDR2_aligned}$	GDDR2 Data Rate	All Devices	—	800	—	700	—	624	Mb/s
$f_{MAX_GDDR2_aligned}$	GDDR2 CLK Frequency	All Devices	—	400	—	350	—	312	MHz
Video DDRX71 Inputs With Clock and Data Aligned at Pin (GDDR71_RX.ECLK) Using PLL Clock Input, Left and Right sides Only Figure 3.11									
$t_{SU_LVDS71_i}$	Data Setup from CLK Input (bit i)	All Devices	—	-0.271	—	-0.39	—	-0.41	ns+(1/2+i) * UI
$t_{HD_LVDS71_i}$	Data Hold from CLK Input (bit i)	All Devices	0.271	—	0.39	—	0.41	—	ns+(1/2+i) * UI
f_{DATA_LVDS71}	DDR71 Data Rate	All Devices	—	756	—	620	—	525	Mb/s
f_{MAX_LVDS71}	DDR71 CLK Frequency (ECLK)	All Devices	—	378	—	310	—	262.5	MHz

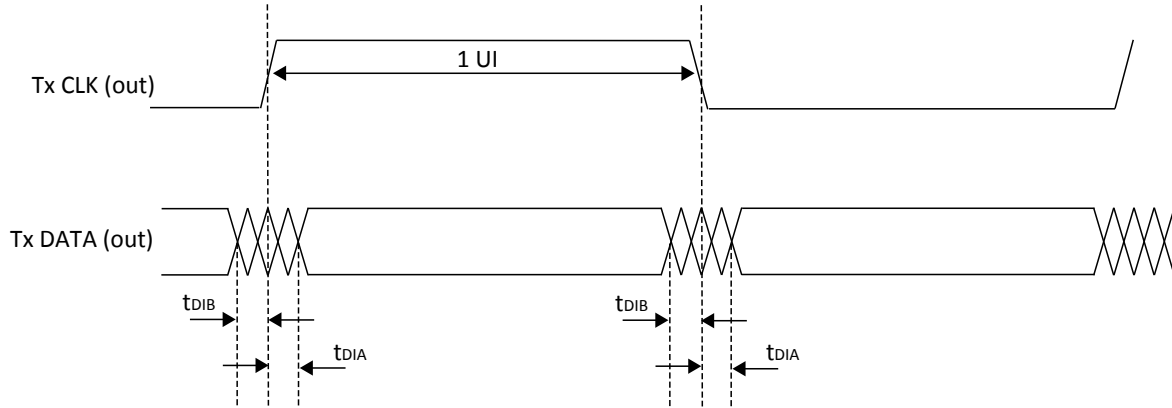
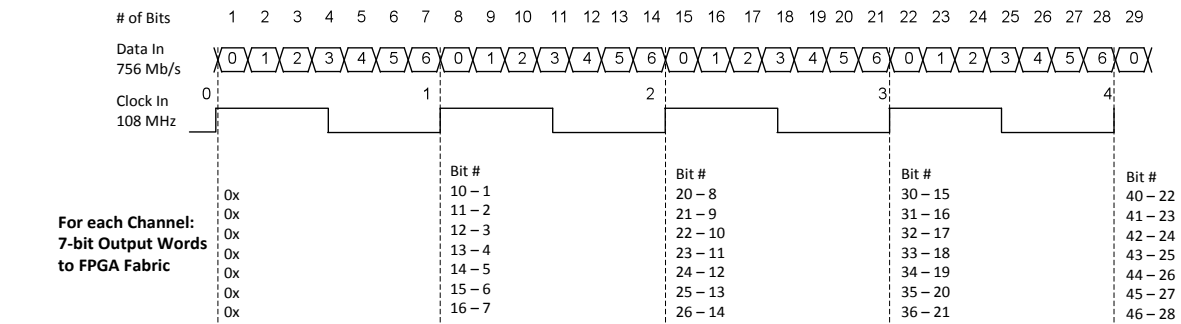


Figure 3.9. Transmit TX.CLK.Aligned Waveforms

Receiver – Shown for one LVDS Channel



Transmitter – Shown for one LVDS Channel

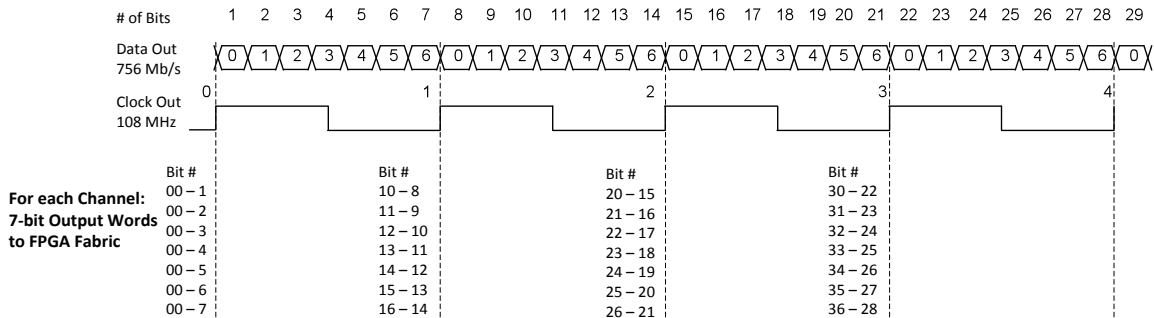


Figure 3.10. DDRX71 Video Timing Waveforms

3.19. sysCLOCK PLL Timing

Over recommended operating conditions.

Table 3.23. sysCLOCK PLL Timing

Parameter	Descriptions	Conditions	Min	Max	Units
f_{IN}	Input Clock Frequency (CLKI, CLKFB)	—	8	400	MHz
f_{OUT}	Output Clock Frequency (CLKOP, CLKOS)	—	3.125	400	MHz
f_{VCO}	PLL VCO Frequency	—	400	800	MHz
f_{PFD}^3	Phase Detector Input Frequency	—	10	400	MHz
AC Characteristics					
t_{DT}	Output Clock Duty Cycle	—	45	55	%
t_{PH4}	Output Phase Accuracy	—	–5	5	%
t_{OPJIT}^1	Output Clock Period Jitter	$f_{OUT} \geq 100$ MHz	—	100	ps p-p
		$f_{OUT} < 100$ MHz	—	0.025	UIPP
	Output Clock Cycle-to-Cycle Jitter	$f_{OUT} \geq 100$ MHz	—	200	ps p-p
		$f_{OUT} < 100$ MHz	—	0.050	UIPP
	Output Clock Phase Jitter	$f_{PFD} \geq 100$ MHz	—	200	ps p-p
		$f_{PFD} < 100$ MHz	—	0.011	UIPP
t_{SPO}	Static Phase Offset	Divider ratio = integer	—	400	ps p-p
t_W	Output Clock Pulse Width	At 90% or 10%	0.9	—	ns
t_{LOCK}^2	PLL Lock-in Time	—	—	15	ms
t_{UNLOCK}	PLL Unlock Time	—	—	50	ns
t_{IPJIT}	Input Clock Period Jitter	$f_{PFD} \geq 20$ MHz	—	1,000	ps p-p
		$f_{PFD} < 20$ MHz	—	0.02	UIPP
t_{HI}	Input Clock High Time	90% to 90%	0.5	—	ns
t_{LO}	Input Clock Low Time	10% to 10%	0.5	—	ns
t_{RST}	RST/ Pulse Width	—	1	—	ms
t_{RSTREC}	RST Recovery Time	—	1	—	ns
t_{LOAD_REG}	Min Pulse for CIB_LOAD_REG	—	10	—	ns
$t_{ROTATE-SETUP}$	Min time for CIB dynamic phase controls to be stable fore CIB_ROTATE	—	5	—	ns
$t_{ROTATE-WD}$	Min pulse width for CIB_ROTATE to maintain “0” or	—	4	—	VCO cycles

Notes:

1. Jitter sample is taken over 10,000 samples for Periodic jitter, and 2,000 samples for Cycle-to-Cycle jitter of the primary PLL output with clean reference clock with no additional I/O toggling.
2. Output clock is valid after t_{LOCK} for PLL reset and dynamic delay adjustment.
3. Period jitter and cycle-to-cycle jitter numbers are guaranteed for $f_{PFD} > 10$ MHz. For $f_{PFD} < 10$ MHz, the jitter numbers may not be met in certain conditions.

3.27. XAUI/CPRI LV E.30 Electrical and Timing Characteristics

3.27.1. AC and DC Characteristics

Over recommended operating conditions.

Table 3.33. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance	—	80	100	120	Ω
$J_{TX_DDJ}^{2,3}$	Output data deterministic jitter	—	—	—	0.17	UI
$J_{TX_TJ}^{1,2,3}$	Total output data jitter	—	—	—	0.35	UI

Notes:

1. Total jitter includes both deterministic jitter and random jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Over recommended operating conditions.

Table 3.34. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL_{RX_DIFF}	Differential return loss	From 100 MHz to 3.125 GHz	10	—	—	dB
RL_{RX_CM}	Common mode return loss	From 100 MHz to 3.125 GHz	6	—	—	dB
Z_{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
$J_{RX_DJ}^{1,2,3}$	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
$J_{RX_RJ}^{1,2,3}$	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
$J_{RX_SJ}^{1,2,3}$	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
$J_{RX_TJ}^{1,2,3}$	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T_{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

3.28. CPRI LV E.24/SGMII(2.5Gbps) Electrical and Timing Characteristics

3.28.1. AC and DC Characteristics

Table 3.35. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T_{RF}^1	Differential rise/fall time	20% to 80%	—	80	—	ps
$Z_{TX_DIFF_DC}$	Differential impedance	—	80	100	120	Ω
$J_{TX_DDJ}^{3,4}$	Output data deterministic jitter	—	—	—	0.17	UI
$J_{TX_TJ}^{2,3,4}$	Total output data jitter	—	—	—	0.35	UI

Notes:

1. Rise and Fall times measured with board trace, connector and approximately 2.5 pf load.
2. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
3. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
4. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Table 3.36. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 2.5 GHz	10	—	—	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 2.5 GHz	6	—	—	dB
Z _{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J _{RX_DJ} ^{2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.37	UI
J _{RX_RJ} ^{2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.18	UI
J _{RX_SJ} ^{2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.10	UI
J _{RX_TJ} ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.65	UI
T _{RX_EYE}	Receiver eye opening	—	0.35	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.29. Gigabit Ethernet/SGMII(1.25Gbps)/CPRI LV E.12 Electrical and Timing Characteristics

3.29.1. AC and DC Characteristics

Table 3.37. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
T _{RF}	Differential rise/fall time	20% to 80%	—	80	—	ps
Z _{TX_DIFF_DC}	Differential impedance	—	80	100	120	Ω
J _{TX_DDJ} ^{2, 3}	Output data deterministic jitter	—	—	—	0.10	UI
J _{TX_TJ} ^{1, 2, 3}	Total output data jitter	—	—	—	0.24	UI

Notes:

1. Total jitter includes both deterministic jitter and random jitter. The random jitter is the total jitter minus the actual deterministic jitter.
2. Jitter values are measured with each CML output AC coupled into a 50 Ω impedance (100 Ω differential impedance).
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.

Table 3.38. Receive and Jitter Tolerance

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
RL _{RX_DIFF}	Differential return loss	From 100 MHz to 1.25 GHz	10	—	—	dB
RL _{RX_CM}	Common mode return loss	From 100 MHz to 1.25 GHz	6	—	—	dB
Z _{RX_DIFF}	Differential termination resistance	—	80	100	120	Ω
J _{RX_DJ} ^{1, 2, 3, 4}	Deterministic jitter tolerance (peak-to-peak)	—	—	—	0.34	UI
J _{RX_RJ} ^{1, 2, 3, 4}	Random jitter tolerance (peak-to-peak)	—	—	—	0.26	UI
J _{RX_SJ} ^{1, 2, 3, 4}	Sinusoidal jitter tolerance (peak-to-peak)	—	—	—	0.11	UI
J _{RX_TJ} ^{1, 2, 3, 4}	Total jitter tolerance (peak-to-peak)	—	—	—	0.71	UI
T _{RX_EYE}	Receiver eye opening	—	0.29	—	—	UI

Notes:

1. Total jitter includes deterministic jitter, random jitter and sinusoidal jitter.
2. Jitter values are measured with each high-speed input AC coupled into a 50 Ω impedance.
3. Jitter and skew are specified between differential crossings of the 50% threshold of the reference signal.
4. Jitter tolerance, Differential Input Sensitivity and Receiver Eye Opening parameters are characterized when Full Rx Equalization is enabled.

3.30. SMPTE SD/HD-SDI/3G-SDI (Serial Digital Interface) Electrical and Timing Characteristics

3.30.1. AC and DC Characteristics

Table 3.39. Transmit

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDO}	Serial data rate	—	270	—	2975	Mb/s
T _{JALIGNMENT} ²	Serial output jitter, alignment	270 Mb/s ⁶	—	—	0.2	UI
T _{JALIGNMENT} ²	Serial output jitter, alignment	1485 Mb/s	—	—	0.2	UI
T _{JALIGNMENT} ^{1, 2}	Serial output jitter, alignment	2970 Mb/s	—	—	0.3	UI
T _{JTIMING}	Serial output jitter, timing	270 Mb/s ⁶	—	—	0.2	UI
T _{JTIMING}	Serial output jitter, timing	1485 Mb/s	—	—	1	UI
T _{JTIMING}	Serial output jitter, timing	2970 Mb/s	—	—	2	UI

Notes:

1. Timing jitter is measured in accordance with SMPTE serial data transmission standards.
2. Jitter is defined in accordance with SMPTE RP1 184-1996 as: jitter at an equipment output in the absence of input jitter.
3. All Tx jitter are measured at the output of an industry standard cable driver, with the Lattice SERDES device configured to 50 Ω output impedance connecting to the external cable driver with differential signaling.
4. The cable driver drives: RL=75 Ω, AC-coupled at 270, 1485, or 2970 Mb/s.
5. All LFE5UM/LFE5UM5G devices are compliant with all SMPTE compliance tests, except 3G-SDI Level-A pathological compliance pattern test.
6. 270 Mb/s is supported with Rate Divider only.

Table 3.40. Receive

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
BR _{SDI}	Serial input data rate	—	270	—	2970	Mb/s

Table 3.41. Reference Clock

Symbol	Description	Test Conditions	Min	Typ	Max	Unit
F _{VCLK}	Video output clock frequency	—	54	—	148.5	MHz
DC _v	Duty cycle, video clock	—	45	50	55	%

Note: SD-SDI (270 Mb/s) is supported with Rate Divider only. For Single Rate: Reference Clock = 54 MHz and Rate Divider = /2. For Tri-Rate: Reference Clock = 148.5 MHz and Rate Divider = /11.

4.2. PICs and DDR Data (DQ) Pins Associated with the DDR Strobe (DQS) Pin

PICs Associated with DQS Strobe	PIO within PIC	DDR Strobe (DQS) and Data (DQ) Pins
For Left and Right Edges of the Device Only		
P[L/R] [n-6]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n-3]	A	DQ
	B	DQ
	C	DQ
	D	DQ
P[L/R] [n]	A	DQS (P)
	B	DQS (N)
	C	DQ
	D	DQ
P[L/R] [n+3]	A	DQ
	B	DQ
	C	DQ
	D	DQ

Note: "n" is a row PIC number.

4.3. Pin Information Summary

4.3.1. LFE5UM/LFE5UM5G

Pin Information Summary		LFE5UM/ LFE5UM5G-25		LFE5UM/LFE5UM5G-45			LFE5UM/LFE5UM5G-85			
Pin Type		285 csfBG	381 caBGA	285 csfBGA	381 caBG	554 caBGA	285 csfBGA	381 caBG	554 caBGA	756 caBGA
General Purpose Inputs/Outputs per Bank	Bank 0	6	24	6	27	32	6	27	32	56
	Bank 1	6	32	6	33	40	6	33	40	48
	Bank 2	21	32	21	32	32	21	34	32	48
	Bank 3	28	32	28	33	48	28	33	48	64
	Bank 4	0	0	0	0	0	0	0	14	24
	Bank 6	26	32	26	33	48	26	33	48	64
	Bank 7	18	32	18	32	32	18	32	32	48
	Bank 8	13	13	13	13	13	13	13	13	13
Total Single-Ended User I/O		118	197	118	203	245	118	205	259	365
VCC		13	20	13	20	24	13	20	24	36
VCCAUX (Core)		3	4	3	4	9	3	4	9	8
VCCIO	Bank 0	1	2	1	2	3	1	2	3	4
	Bank 1	1	2	1	2	3	1	2	3	4
	Bank 2	2	3	2	3	4	2	3	4	4
	Bank 3	2	3	2	3	3	2	3	3	4
	Bank 4	0	0	0	0	0	0	0	2	2
	Bank 6	2	3	2	3	4	2	3	4	4
	Bank 7	2	3	2	3	3	2	3	3	4
	Bank 8	2	2	2	2	2	2	2	2	2

Supplemental Information

For Further Information

A variety of technical notes for the ECP5/ECP5-5G family are available.

- [High-Speed PCB Design Considerations \(TN1033\)](#)
- [Transmission of High-Speed Serial Signals Over Common Cable Media \(TN1066\)](#)
- [PCB Layout Recommendations for BGA Packages \(TN1074\)](#)
- [Minimizing System Interruption During Configuration Using TransFR Technology \(TN1087\)](#)
- [Electrical Recommendations for Lattice SERDES \(FPGA-TN-02077\)](#)
- [LatticeECP3, ECP-5 and ECP5-5G Soft Error Detection \(SED\)/Correction \(SEC\) Usage Guide \(TN1184\)](#)
- [Using TraceID \(TN1207\)](#)
- [Sub-LVDS Signaling Using Lattice Devices \(TN1210\)](#)
- [Advanced Security Encryption Key Programming Guide for ECP5, ECP5-5G, LatticeECP3, and LatticeECP2/MS Devices \(TN1215\)](#)
- [LatticeECP3, LatticeECP2/M, ECP5 and ECP5-5G Dual Boot and Multiple Boot Feature \(TN1216\)](#)
- [ECP5 and ECP5-5G sysCONFIG Usage Guide \(TN1260\)](#)
- [ECP5 and ECP5-5G SERDES/PCS Usage Guide \(TN1261\)](#)
- [ECP5 and ECP5-5G sysIO Usage Guide \(TN1262\)](#)
- [ECP5 and ECP5-5G sysClock PLL/DLL Design and Usage Guide \(TN1263\)](#)
- [ECP5 and ECP5-5G Memory Usage Guide \(TN1264\)](#)
- [ECP5 and ECP5-5G High-Speed I/O Interface \(TN1265\)](#)
- [Power Consumption and Management for ECP5 and ECP5-5G Devices \(TN1266\)](#)
- [ECP5 and ECP5-5G sysDSP Usage Guide \(TN1267\)](#)
- [ECP5 and ECP5-5G Hardware Checklist \(FPGA-TN-02038\)](#)
- [Solder Reflow Guide for Surface Mount Devices \(FPGA-TN-02041\)](#)
- [ECP5 and ECP5-5G PCI Express Soft IP Ease of Use Guidelines \(FPGA-TN-02045\)](#)
- [Programming External SPI Flash through JTAG for ECP5/ECP5-5G \(FPGA-TN-02050\)](#)
- [Adding Scalable Power and Thermal Management to ECP5 Using L-ASC10 \(AN6095\)](#)

For further information on interface standards refer to the following websites:

- JEDEC Standards (LVTTTL, LVCMOS, SSTL): www.jedec.org
- PCI: www.pcisig.com

(Continued)

Date	Version	Section	Change Summary
April 2017	1.7	All	Changed document number from DS1044 to FPGA-DS-02012.
		General Description	Updated Features section. Changed “1.1 V core power supply” to “1.1 V core power supply for ECP5, 1.2 V core power supply for ECP5UM5G”.
		Architecture	Updated Overview section. Change “The ECP5/ECP5-5G devices use 1.1 V as their core voltage” to “The ECP5 devices use 1.1V, ECP5UM5G devices use 1.2V as their core voltage”
		DC and Switching Characteristics	Updated Table 3.2. Recommended Operating Conditions Added ECP5-5G on VCC to be 1.2V +/- 5% Added ECP5-5G on VCCA to be 1.2V +/- 3% Updated Table 3.8. ECP5/ECP5-5G Supply Current (Standby) Changed “Core Power Supply Current” for ICC on LFE5UM5G devices Changed “SERDES Power Supply Current (Per Dual)” for ICCA on LFE5UM5G devices Updated Table 3.20. Register-to-Register Performance. Remove “(DDR/SDR)” from DSP Function Changed DSP functions to 225 MHz
		Pinout Information	Update Section 4.1 Signal Description. Revised Vcc Description to “Power supply pins for core logic. Dedicated pins. VCC = 1.1 V (ECP5), 1.2 V (ECP5UM5G)”
February 2016	1.6	All	Changed document status from Preliminary to Final.
		General Description	Updated Features section. Changed “24K to 84K LUTs” to “12K to 84K LUTs”. Added LFE5U-12 column to Table 1.1. ECP5 and ECP5-5G Family Selection Guide.
		DC and Switching Characteristics	Updated Power up Sequence section. Identified typical ICC current for specific devices in Table 3.8. ECP5/ECP5-5G Supply Current (Standby). Updated values in Table 3.9. ECP5. Updated values in Table 3.10. ECP5-5G. Added values to –8 Timing column of Table 3.19. Pin-to-Pin Performance. Added values to –8 Timing column of Table 3.20. Register-to-Register Performance. Changed LFE5-45 to All Devices in Table 3.22. ECP5/ECP5-5G External Switching Characteristics. Added table notes to Table 3.31. PCIe (5 Gb/s). Added table note to Table 3.32. CPRI LV2 E.48 Electrical and Timing Characteristics.
		Pinout Information	Added LFE5U-12 column to the table in LFE5U section.
		Ordering Information	Updated LFE5U in ECP5/ECP5-5G Part Number Description section: added 12 F = 12K LUTs to Logic Capacity. Added LFE5U-12F information to Ordering Part Numbers section.

(Continued)

Date	Version	Section	Change Summary
November 2015	1.5	All	Added ECP5-5G device family.
			Changed document title to ECP5 and ECP5-5G Family Data Sheet.
	1.4	General Description	Updated Features section. Added support for eDP in RDR and HDR.
		Architecture	Updated Overview section. Revised Figure 2.1. Simplified Block Diagram, LFE5UM/LFE5UM5G-85 Device (Top Level). Modified Flexible sysIO description and Note.
			Updated SERDES and Physical Coding Sublayer section. - Changed E.24.V in CPRI protocol to E.24.LV. - Removed “1.1 V” from paragraph on unused Dual.
		DC and Switching Characteristics	Updated Hot Socketing Requirements section. Revised V _{CCHTX} in table notes 1 and 3. Indicated V _{CCHTX} in table note 4.
			Updated SERDES High-Speed Data Transmitter section. Revised V _{CCHTX} in table note 1.
		Ordering Information	Updated ECP5/ECP5-5G Part Number Description section. Changed “LFE5 FPGA” under Device Family to “ECP5 FPGA”.
August 2015	1.3	General Description	Updated Features section. - Removed SMPTE3G under Embedded SERDES. - Added Single Event Upset (SEU) Mitigation Support. Removed SMPTE protocol in fifth paragraph.
		Architecture	General update.
		DC and Switching Characteristics	General update.
		Pinout Information	Updated Signal Descriptions section. Revised the descriptions of the following signals: - P[L/R] [Group Number]_[A/B/C/D] - P[T/B][Group Number]_[A/B] - D4/IO4 (Previously named D4/MOSI2/IO4) - D5/IO5 (Previously named D5/MISO/IO5) - VCCHRX_D[dual_num]CH[chan_num] - VCCHTX_D[dual_num]CH[chan_num]
		Supplemental Information	Added TN1184 reference.